

Atty Docket No 100-22900 [P05685]

DECLARATION FOR PATENT APPLICATION

As a below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name,

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled

on the invention entitled				
HIGH-VOLTAGE SILICON	CONTROLLED RECTIFIER	STRUCTURE		
the specification of which (check one) X is attached hereto or was filed on as Application No. and was amended on (if applicable). thereby state that I have reviewed and understand the contents of the above-identified specification, including the claims, as amended by any amendment referred to above.				
patent or inventor's certification country other than the Unite	ite, or § 365(a) of any PCT In ed States, listed below and ha	119(a)-(d) or § 365(b) of any foreign ternational application which designave also identified below any foreign that of the application on which prio	ated at least one application for	
Prior Foreign Application(s)			Priority Claimed Yes No	
Number	Country	Day/Month/Year Filed		
I hereby claim the benefit u	nder 35 U.S.C. § 119(e) of a	ny United States provisional applicat	ion(s) below.	
Application Number	Filing Date			
Application Number	Filing Date			
International application de the claims of this application first paragraph of 35 U.S.C patentability as defined in 3	signating the United States, I n is not disclosed in the prior . § 112, I acknowledge the du	United States application(s), or § 36 isted below and, insofar as the subject United States application in the marty to disclose all information which is available between the filing date of oplication:	ct matter of each of nner provided by the s material to	
Application Number	Filing Date	Status: Patented, Pending,	Abandoned	
Application Number	Filing Date	Status: Patented, Pending	Abandoned	

PATENT

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I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

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